



TO-220F Plastic-Encapsulate Transistors

3DA4793 TRANSISTOR (NPN)

FEATURES

- High Transition Frequency : $f_T=100\text{MHz}(\text{Typ})$
- Complementary to 3CA1837
- Collector Power Dissipation
 $P_{CM} : 2\text{W} (T_{amb}=25^\circ\text{C})$
 $20\text{ W} (T_{case}=25^\circ\text{C})$



MAXIMUM RATINGS* $T_A=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	230	V
V_{CEO}	Collector-Emitter Voltage	230	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current -Continuous	1000	mA
I_B	Base Current	100	mA
T_J	Junction Junction	150	$^\circ\text{C}$
T_{stg}	Storage Junction	-55-150	$^\circ\text{C}$

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

ELECTRICAL CHARACTERISTICS ($T_{amb}=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=0.1\text{mA}, I_E=0$	230			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=1\text{mA}, I_B=0$	230			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=100\mu\text{A}, I_C=0$	5			V
Collector cut-off current	I_{CBO}	$V_{CB}=230\text{V}, I_E=0$			10	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=5\text{V}, I_C=0$			10	μA
DC current gain	h_{FE}	$V_{CE}=5\text{V}, I_C=100\text{mA}$	100		320	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=500\text{mA}, I_B=50\text{mA}$			1.5	V
Transition frequency	f_T	$V_{CE}=10\text{V}, I_C=100\text{mA}$	30			MHz

